



US1AU THRU US1MU

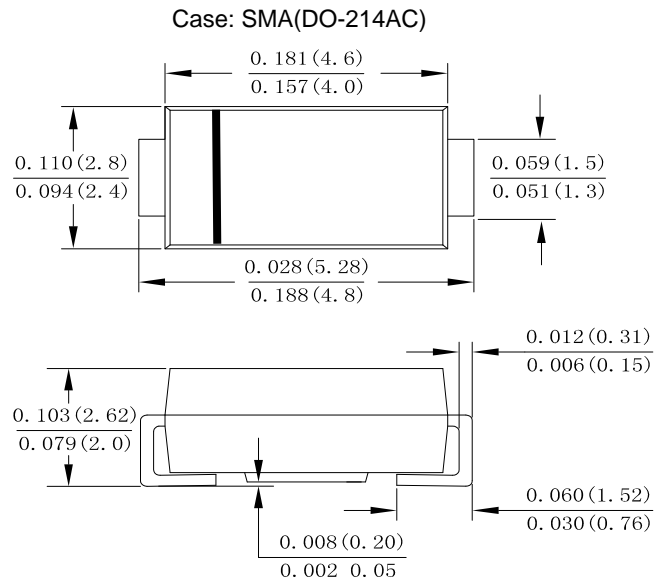
1.0AMP Ultra Fast Recovery Silicon Rectifier

Features

- Low Power Loss, High Efficiency
- Ideally Suited for Automatic Assembly
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: Molded plastic SMA
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026 guaranteed
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Making: Type Number



Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load

For capacitive load derate current by 20%

Type Number	SYMBOL	US1AU	US1BU	US1DU	US1GU	US1JU	US1KU	US1MU	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Average Rectified Output Current @ $T_L = 100^\circ\text{C}$	$I_{F(AV)}$	1.0							A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	35							A
Rating for fusing ($t < 8.3\text{ms}$)	$I^2 t$	5.08							A^2s
Forward Voltage @ $I_F = 1.0\text{A}$	V_{FM}	1.0		1.3		1.7		V	
Peak Reverse Current @ $T_A = 25^\circ\text{C}$	I_R	5.0							uA
At Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$		200							
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50				75			ns
Typical Junction Capacitance (Note 2)	C_J	20							pF
Typical Thermal Resistance Junction to Ambient (Note 3)	$R_{\theta JA}$	70							$^\circ\text{C}/\text{W}$
Operating Temperature Range	T_J	-55 to +150							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150							$^\circ\text{C}$

Note:

1. Reverse Recovery Test Conditions: $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $IRR = 0.25\text{A}$.
2. Measured at 1.0 MHz and Applied reverse Voltage of 4.0V D.C
3. Device mounted on FR-4 substrate, 1" x 1", 2oz, single-sided, PC boards with 0.1" x 0.15" copper pad.



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FIG.1 MAXIMUM AVERAGE FORWARD CURRENT DERATING

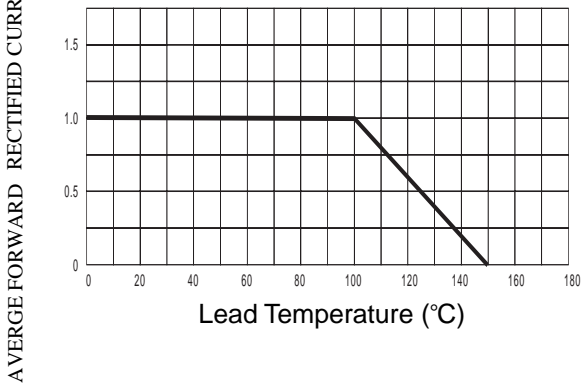


FIG.2 TYPICAL FORWARD CHARACTERISTICS

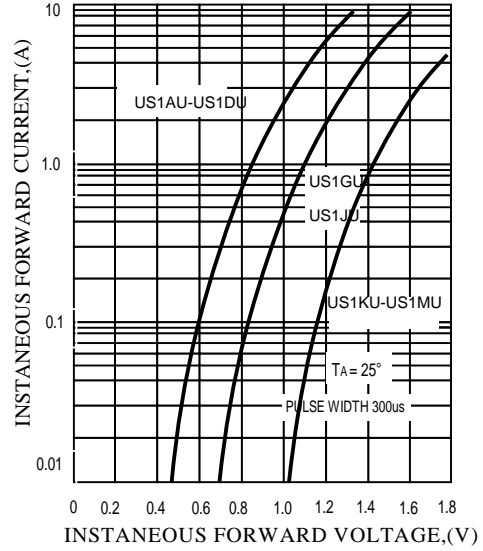


FIG.3 MAXIMUM NON-REPEITIVE SURGE CURRENT

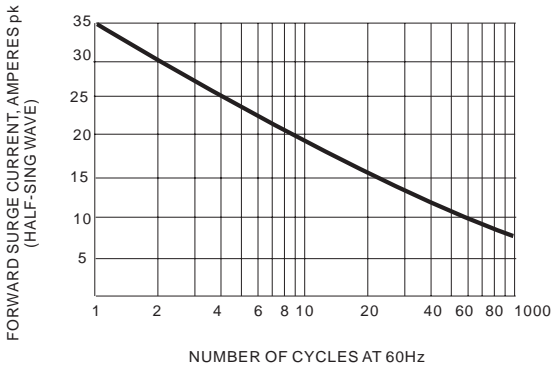


FIG.4 TYPICAL JUNCTION CAPACITANCE

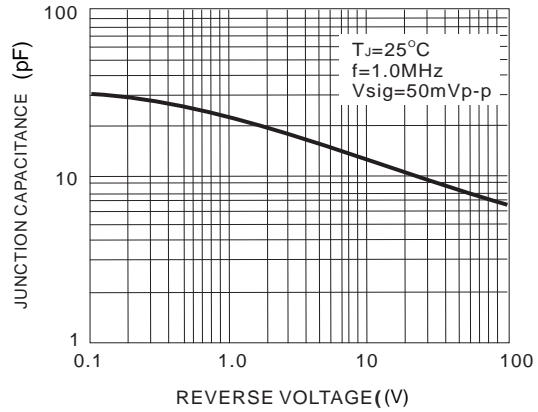
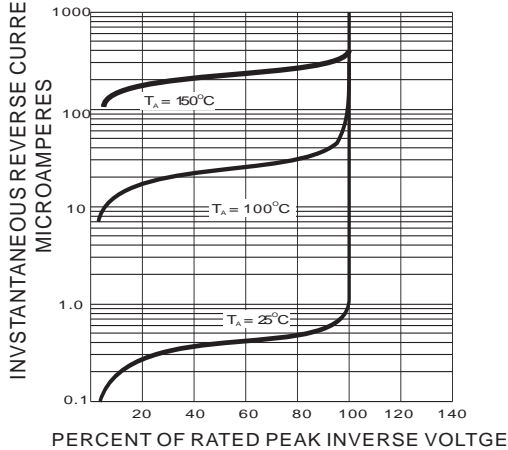
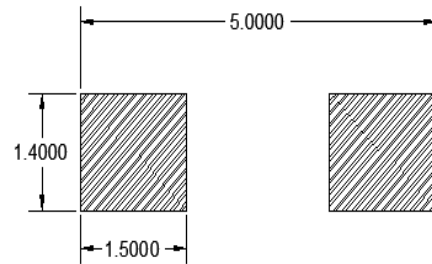


FIG.5 TYPICAL REVERSE CHARACTERISTICS



SMA PAD LAYOUT





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